ABSTRACT OF THE DISCLOSURE

A method is presented for forming pores within a central area of a semi-conductive or conductive surface. The method includes forming a semi-conductive or conductive surface on a substrate. This semi-conductive or conductive surface is formed in a manner ensuring that upon application of an electric field at the semi-conductive or conductive surface an intensity of the electric field at a central area of the surface is at least as great as an intensity of the electric field at a perimeter of the surface. Finally, the method includes anodizing the semi-conductive or conductive surface by generating the electric field at the semi-conductive or conductive surface to form a porous region within the semi-conductive or conductive surface.

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